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Manufacturers of World Class Discrete Semiconductors

2N4248
2N4249
2N4250
2N4250A

SILICON PNP TRANSISTOR

JEDEC TO-106 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4248 Series Types are Silicon PNP Transistors designed for low level - low noise amplifier applications.

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	2N4248 2N4250	2N4249 2N4250A	UNIT
Collector-Base Voltage	V_{CBO}	40	60	V
Collector-Emitter Voltage	V_{CES}	40	60	V
Collector-Emitter Voltage	V_{CEO}	40	60	V
Emitter-Base Voltage	V_{EBO}	5.0	5.0	V
Power Dissipation	P_D	200	200	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 TO +150		°C

ELECTRICAL CHARACTERISTICS (T_A=25°C)

SYMBOL		2N4248 MIN	2N4248 MAX	2N4249 MIN	2N4249 MAX	2N4250 MIN	2N4250 MAX	2N4250A MIN	2N4250A MAX	UNIT
I_{CBO}	V_{CB}=40V (2N4250A V_{CB}=50V)		10		10		10		10	nA
I_{EBO}	V_{EB}=3.0V		20		20		20		20	nA
BV_{CBO}	I_C=10μA	40		60		40		60		V
BV_{CES}	I_C=10μA	40		60		40		60		V
BV_{CEO}	I_C=5.0mA	40		60		40		60		V
BV_{EBO}	I_E=10μA	5.0		5.0		5.0		5.0		V
$V_{CE(s)}$	I_C=10mA, I_B=0.5mA		0.25		0.25		0.25		0.25	V
$V_{BE(s)}$	I_C=10mA, I_B=0.5mA		0.9		0.9		0.9		0.9	V
h_{FE}	V_{CE}=5.0V, I_C=100μA	50		100	300	250	700	250	700	
h_{FE}	V_{CE}=5.0V, I_C=1.0mA	50		100		250		---		
h_{FE}	V_{CE}=5.0V, I_C=10mA	50		100		250		---		
f_T	V_{CE}=5.0V, I_C=0.5mA, f=20MHz	40		40		50		---		MHz
C_{ob}	V_{CB}=5.0V, f=1.0MHz		6.0		6.0		6.0		6.0	pF
C_{IB}	V_{EB}=0.5V, f=1.0MHz		16		16		16		---	pF
NF	Wide Band, V_{CE}=5.0V, I_C=20μA, Rs=100KΩ PBW=15.7kHz, f=10Hz TO 10kHz		---		3.0		2.0		2.0	dB
NF	Narrow Band, V_{CE}=5.0V, I_C=20μA, Rs=10KΩ PBW=150Hz, f=1.0kHz		---		3.0		2.0		2.0	dB